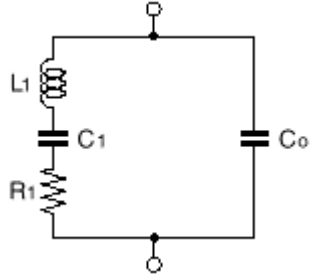


Passive Components

Resistor	$V = I.R$
Capacitor	<p>Time Domain: $i_C(t) = C \cdot \frac{dv_C(t)}{dt}$ or $v_C(t) = v_C(t_0) + \frac{1}{C} \int_{t_0}^t i_C(\tau) d\tau$</p> <p>Frequency Domain: $z = \frac{1}{j.\omega.C}$</p> <p>S Domain: $z = \frac{1}{s.C}$</p> <p>S Domain with Initial Voltage: - Parallel Current Source $I = +C.V_C(0^-)$</p> <p style="text-align: right;">Series Voltage source $V = \frac{+V_C(0^-)}{s}$</p>
Inductor	<p>Time Domain: $v_L(t) = L \cdot \frac{di_L(t)}{dt}$ or $i_L(t) = i_L(t_0) + \frac{1}{L} \int_{t_0}^t v_L(\tau) d\tau$</p> <p>Frequency Domain: $z = j.\omega.L$</p> <p>S Domain: $z = s.L$</p> <p>S Domain with Initial Current: - Parallel Current Source $I = \frac{-i_L(0^-)}{s}$</p> <p style="text-align: right;">Series Voltage source $V = -L.i_L(0^-)$</p>
Quartz Crystal	<div style="display: flex; align-items: flex-start;"> <div style="flex: 1;">  </div> <div style="flex: 2; padding-left: 20px;"> <p>L_1 = Dynamic or motional Inductance (mH)</p> <p>C_1 = Dynamic or motional Capacitance (fF - Fempto Farads)</p> <p>R_1 = Equivalent Series Resistance (Ω)</p> <p>C_0 = Parallel or Static Capacitance (pF) (holder capacitance)</p> </div> </div> <p style="margin-top: 20px;">Series Resonant Frequency $f_s = \frac{1}{2\pi\sqrt{L_1 C_1}}$</p> <p>Parallel Resonant Frequency $f_p = \frac{1}{2\pi\sqrt{\frac{L_1 C_1 C_0}{C_1 + C_0}}}$</p> <p style="text-align: center;">$\approx f_s \left(1 + \frac{1}{2\gamma} \right)$</p> <p>Capacitance Ratio $\gamma = \frac{C_0}{C_1}$</p> <p>Quality Factor $Q = \frac{2\pi f_s L_1}{R_1} = \frac{1}{2\pi f_s C_1 R_1}$</p> <p>Figure of Merit $M = \frac{Q}{\gamma} = \frac{1}{2\pi f_s C_0 R_1}$</p>

Polyswitch	$m.C_p \left(\frac{\Delta T}{\Delta t} \right) = I^2 R - U(T - T_a)$ <p>or :</p> $R = \frac{m.C_p \left(\frac{\Delta T}{\Delta t} \right) + U(T - T_a)}{I^2}$ <p>m = Mass of device (Kg) C_p = Heat capacity of device (J.Kg⁻¹.°K⁻¹) ΔT = Change in Temperature of device (°K) Δt = Change in time (s) I = Current flowing through device (Amps) R = Resistance of device (Ω) U = Overall Heat Transfer Coefficient (W.°K⁻¹) T = Temperature of device (°K) T_a = Ambient Temperature (°K)</p>
Metal Oxide Varistor (MOV)	$I = k.V^\alpha$ <p>Where: k = constant dependent on geometry α = Nonlinear Exponent - Can be determined from two V - I points :</p> $\alpha = \frac{\log(I_1 / I_2)}{\log(V_1 / V_2)}$